

An electro-optical device includes a substrate on which a TFT, a data line, a scanning line, a capacitance line, a first intermediate conductive layer, a second intermediate conductive layer, and a pixel electrode are formed. A first contact hole, via which the drain of the TFT and the first intermediate conductive layer are connected to each other, is formed in an area which overlaps, in plan view, with the data line. The above-described structure of this electro-optical device, which includes the intermediate conductive layer disposed between the pixel electrode and the pixel switching TFT, allows an increase in the pixel aperture ratio and also an increase in the storage capacitance. Besides, degradation in the quality of a displayed image due to steps formed, in the vicinity of the pixel electrode, on the surface of an alignment film is minimized.